

Silicon NPN Power Transistors

2SD1265 2SD1265A

DESCRIPTION

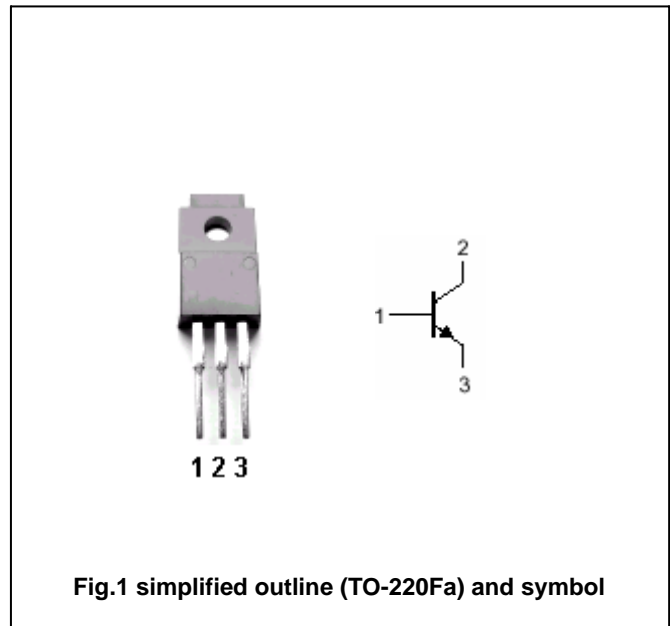
- With TO-220Fa package
- Low collector saturation voltage
- Wide area of safe operation

APPLICATIONS

- For audio frequency power applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SD1265	60	V
		2SD1265A	80	
V_{CEO}	Collector-emitter voltage	2SD1265	60	V
		2SD1265A	80	
V_{EBO}	Emitter-base voltage	Open collector	8	V
I_C	Collector current (DC)		4	A
I_{CM}	Collector current-peak		6	A
I_B	Base current		1	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	30	W
		$T_a=25^\circ\text{C}$	2	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	2SD1265	I _C =0.2A, L=25mH	60			V
		2SD1265A		80			
V _{CEsat}	Collector-emitter saturation voltage		I _C =2A; I _B =0.4A			1.0	V
V _{BE}	Base-emitter on voltage		I _C =1A; V _{CE} =3V			1.2	V
I _{CBO}	Collector cut-off current		V _{CB} =20V; I _E =0			30	μ A
I _{EBO}	Emitter cut-off current		V _{EB} =8V; I _C =0			1	mA
h _{FE-1}	DC current gain		I _C =0.1A; V _{CE} =3V	40			
h _{FE-2}	DC current gain		I _C =1A; V _{CE} =3V	30		160	

◆ h_{FE-2} Classifications

Q	P	O
30-60	500-100	80-160

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PACKAGE OUTLINE

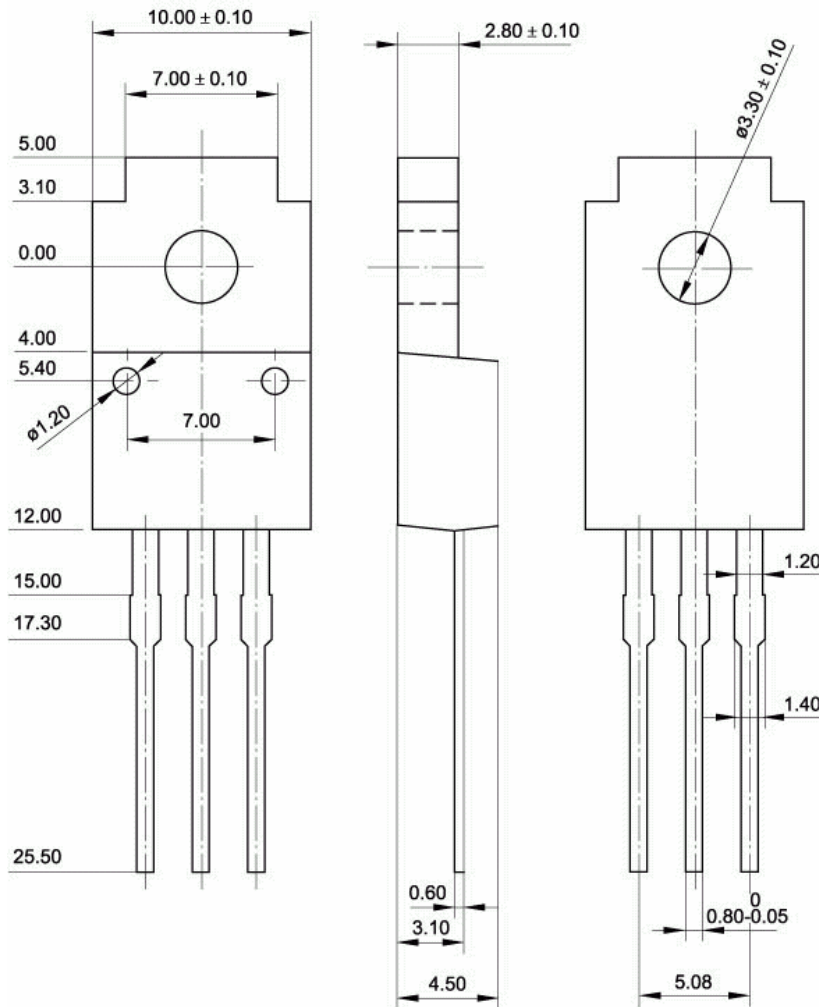


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)